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NTLJD3182FZ

Power MOSFET and Schottky Diode

-20 V, -4.0 A, Single P-Channel & Schottky Barrier Diode, ESD

Features

- WDFN 2x2 mm Package with Exposed Drain Pads for Excellent Thermal Conduction
- Lowest $R_{DS(on)}$ Solution in 2x2 mm Package
- Footprint Same as SC-88 Package
- Low Profile (< 0.8 mm) for Easy Fit in Thin Environments
- ESD Protected
- High Current Schottky Diode: 2 A Current Rating
- This is a Pb-Free Device

Applications

- Optimized for Battery and Load Management Applications in Portable Equipment
- Li-Ion Battery Charging and Protection Circuits
- DC-DC Buck Circuit

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter		Symbol	Value	Unit
Drain-to-Source Voltage		V_{DSS}	-20	V
Gate-to-Source Voltage		V_{GS}	± 8.0	V
Continuous Drain Current (Note 1)	Steady State	$T_A = 25^\circ\text{C}$	-3.2	A
		$T_A = 85^\circ\text{C}$	-2.3	
	$t \leq 5$ s	$T_A = 25^\circ\text{C}$	-4.0	
Power Dissipation (Note 1)	Steady State	$T_A = 25^\circ\text{C}$	1.5	W
		$t \leq 5$ s	2.3	
Continuous Drain Current (Note 2)	Steady State	$T_A = 25^\circ\text{C}$	-2.2	A
		$T_A = 85^\circ\text{C}$	-1.6	
		$T_A = 25^\circ\text{C}$	0.71	
Power Dissipation (Note 2)		P_D	0.71	W
Pulsed Drain Current	$t_p = 10 \mu\text{s}$	I_{DM}	-16	A
Operating Junction and Storage Temperature		T_J, T_{STG}	-55 to 150	$^\circ\text{C}$
Source Current (Body Diode) (Note 2)		I_S	-1.0	A
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)		T_L	260	$^\circ\text{C}$

SCHOTTKY MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise stated)

Parameter	Symbol	Value	Unit
Peak Repetitive Reverse Voltage	V_{RRM}	30	V
DC Blocking Voltage	V_R	30	V
Average Rectified Forward Current	I_F	2.0	A

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Surface Mounted on FR4 Board using 1 in sq pad size (Cu area = 1.127 in sq [2 oz] including traces).
2. Surface Mounted on FR4 Board using the minimum recommended pad size, (30 mm², 2 oz Cu).



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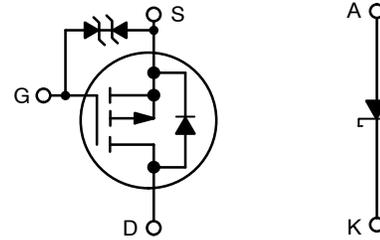
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P-CHANNEL MOSFET

$V_{(BR)DSS}$	$R_{DS(on)}$ Max	I_D Max
-20 V	100 m Ω @ -4.5 V	-4.0 A
	144 m Ω @ -2.5 V	
	200 m Ω @ -1.8 V	

SCHOTTKY DIODE

V_R Max	V_F Max	I_F Max
20 V	0.47 V	2.0 A

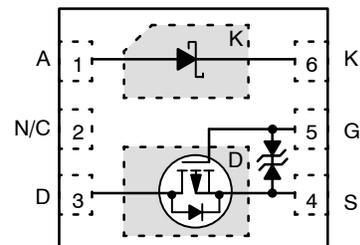


P-CHANNEL MOSFET SCHOTTKY DIODE



JJ = Specific Device Code
M = Date Code
▪ = Pb-Free Package
(Note: Microdot may be in either location)

PIN CONNECTIONS



(Top View)

ORDERING INFORMATION

See detailed ordering and shipping information on page 3 of this data sheet.

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THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Unit
Junction-to-Ambient – Steady State (Note 3)	$R_{\theta JA}$	83	°C/W
Junction-to-Ambient – Steady State Min Pad (Note 4)	$R_{\theta JA}$	177	
Junction-to-Ambient – $t \leq 5$ s (Note 3)	$R_{\theta JA}$	54	

3. Surface Mounted on FR4 Board using 1 in sq pad size (Cu area = 1.127 in sq [2 oz] including traces).
 4. Surface Mounted on FR4 Board using the minimum recommended pad size (30 mm², 2 oz Cu).

MOSFET ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = -250\ \mu\text{A}$	-20			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$	$I_D = -250\ \mu\text{A}$, Ref to 25°C		13		mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -16\text{ V}, V_{GS} = 0\text{ V}$			-1.0	μA
					-10	
Gate-to-Source Leakage Current	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 8.0\text{ V}$			± 10	μA

ON CHARACTERISTICS (Note 5)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = -250\ \mu\text{A}$	-0.4		-1.0	V
Gate Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$			2.0		mV/°C
Drain-to-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = -4.5\text{ V}, I_D = -2.0\text{ A}$		68	100	m Ω
		$V_{GS} = -2.5\text{ V}, I_D = -2.0\text{ A}$		90	144	
		$V_{GS} = -1.8\text{ V}, I_D = -1.7\text{ A}$		125	200	
Forward Transconductance	g_{FS}	$V_{DS} = -16\text{ V}, I_D = -2.0\text{ A}$		6.5		S

CHARGES, CAPACITANCES AND GATE RESISTANCE

Input Capacitance	C_{ISS}	$V_{GS} = 0\text{ V}, f = 1.0\text{ MHz}, V_{DS} = -10\text{ V}$		450		pF
Output Capacitance	C_{OSS}			90		
Reverse Transfer Capacitance	C_{RSS}			62		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = -4.5\text{ V}, V_{DS} = -10\text{ V}, I_D = -2.0\text{ A}$		5.2	7.8	nC
Threshold Gate Charge	$Q_{G(TH)}$			0.3		
Gate-to-Source Charge	Q_{GS}			0.84		
Gate-to-Drain Charge	Q_{GD}			1.5		

SWITCHING CHARACTERISTICS (Note 6)

Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = -4.5\text{ V}, V_{DD} = -5.0\text{ V}, I_D = -2.0\text{ A}, R_G = 2.0\ \Omega$		6.6		ns
Rise Time	t_r			9.0		
Turn-Off Delay Time	$t_{d(OFF)}$			14		
Fall Time	t_f			12.5		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Recovery Voltage	V_{SD}	$V_{GS} = 0\text{ V}, I_S = -1.0\text{ A}$	$T_J = 25^\circ\text{C}$	-0.73	-1.0	V
			$T_J = 125^\circ\text{C}$	-0.62		
Reverse Recovery Time	t_{RR}	$V_{GS} = 0\text{ V}, dI_{SD}/dt = 100\text{ A}/\mu\text{s}, I_S = -1.0\text{ A}$		23		ns
Charge Time	t_a			13		
Discharge Time	t_b			10		
Reverse Recovery Time	Q_{RR}			10		nC

5. Pulse Test: Pulse Width $\leq 300\ \mu\text{s}$, Duty Cycle $\leq 2\%$.
 6. Switching characteristics are independent of operating junction temperatures.

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SCHOTTKY DIODE ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Maximum Instantaneous Forward Voltage	V_F	$I_F = 100 \text{ mA}$		0.34	0.39	V
		$I_F = 1.0 \text{ A}$		0.47	0.53	
Maximum Instantaneous Reverse Current	I_R	$V_R = 30 \text{ V}$		17	20	μA
		$V_R = 20 \text{ V}$		3.0	8.0	
		$V_R = 10 \text{ V}$		2.0	4.5	
Capacitance	C	$V_R = 5.0 \text{ V}, f = 1.0 \text{ MHz}$		38		pF

SCHOTTKY DIODE ELECTRICAL CHARACTERISTICS ($T_J = 85^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Maximum Instantaneous Forward Voltage	V_F	$I_F = 100 \text{ mA}$		0.22	0.35	V
		$I_F = 1.0 \text{ A}$		0.40	0.50	
Maximum Instantaneous Reverse Current	I_R	$V_R = 30 \text{ V}$		0.22	2.5	mA
		$V_R = 20 \text{ V}$		0.11	1.6	
		$V_R = 10 \text{ V}$		0.06	1.2	

SCHOTTKY DIODE ELECTRICAL CHARACTERISTICS ($T_J = 125^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Maximum Instantaneous Forward Voltage	V_F	$I_F = 100 \text{ mA}$		0.20	0.29	V
		$I_F = 1.0 \text{ A}$		0.40	0.47	
Maximum Instantaneous Reverse Current	I_R	$V_R = 30 \text{ V}$		2.0	20	mA
		$V_R = 20 \text{ V}$		1.1	10.9	
		$V_R = 10 \text{ V}$		0.63	8.4	

ORDERING INFORMATION

Device Order Number	Package Type	Tape & Reel Size†
NTLJD3182FZTAG	WDFN6 (Pb-Free)	3000 / Tape & Reel
NTLJD3182FZTBG	WDFN6 (Pb-Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

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TYPICAL PERFORMANCE CURVES ($T_J = 25^\circ\text{C}$ unless otherwise noted)

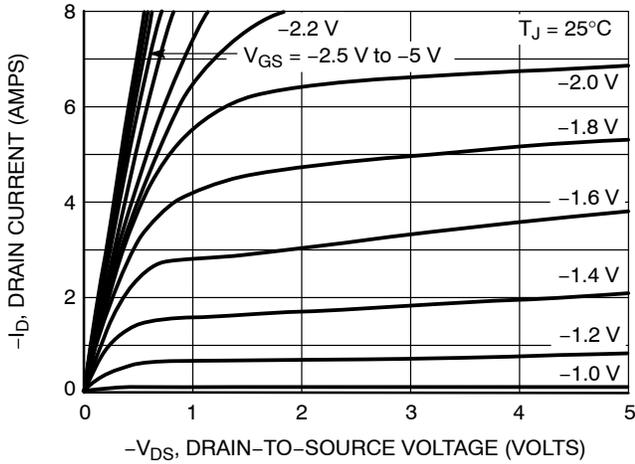


Figure 1. On-Region Characteristics

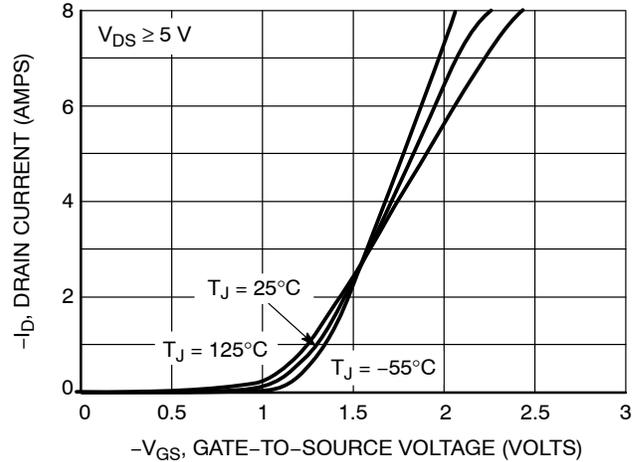


Figure 2. Transfer Characteristics

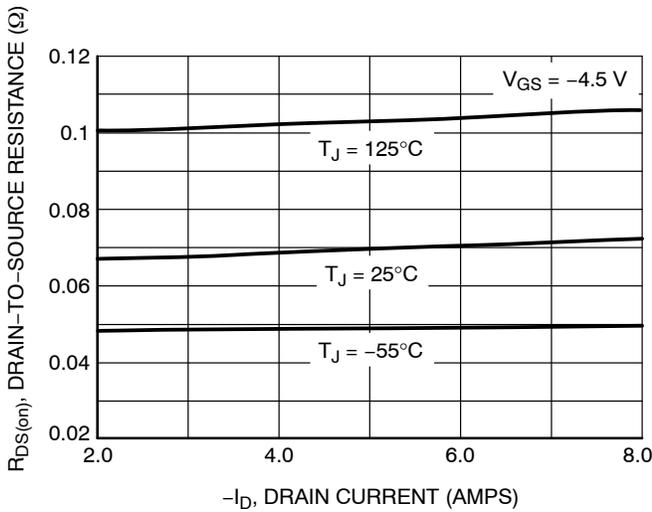


Figure 3. On-Resistance versus Drain Current

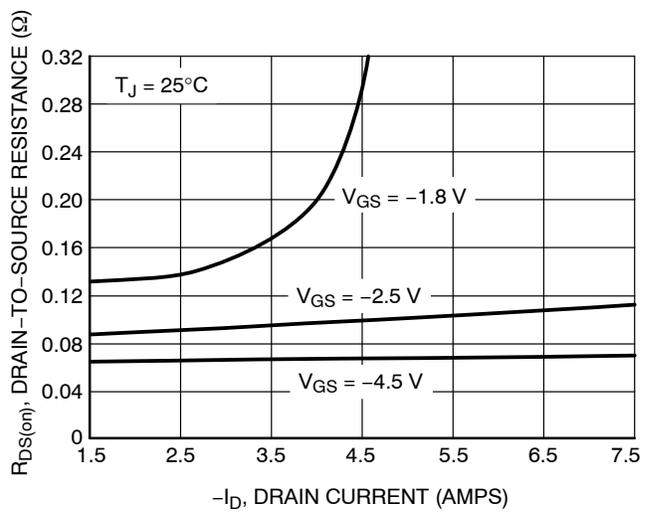


Figure 4. On-Resistance versus Drain Current and Gate Voltage

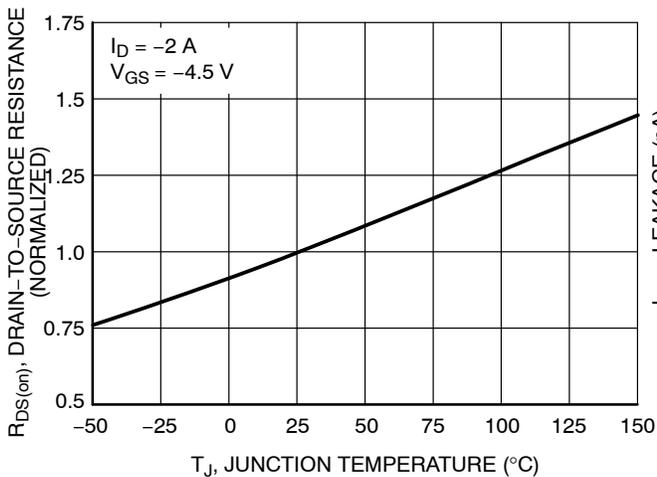


Figure 5. On-Resistance Variation with Temperature

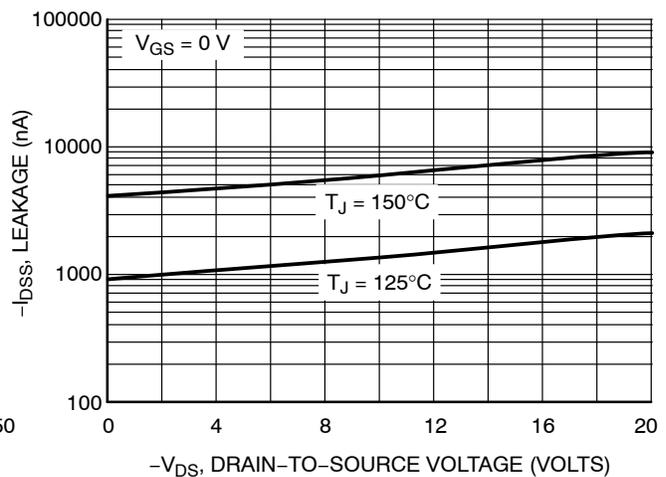


Figure 6. Drain-to-Source Leakage Current versus Voltage

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TYPICAL PERFORMANCE CURVES ($T_J = 25^\circ\text{C}$ unless otherwise noted)

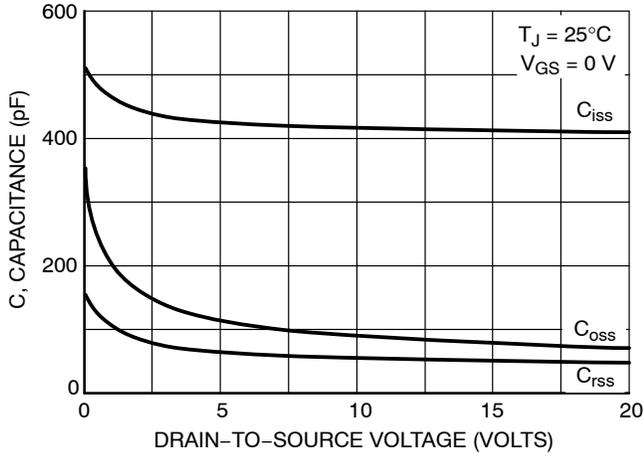


Figure 7. Capacitance Variation

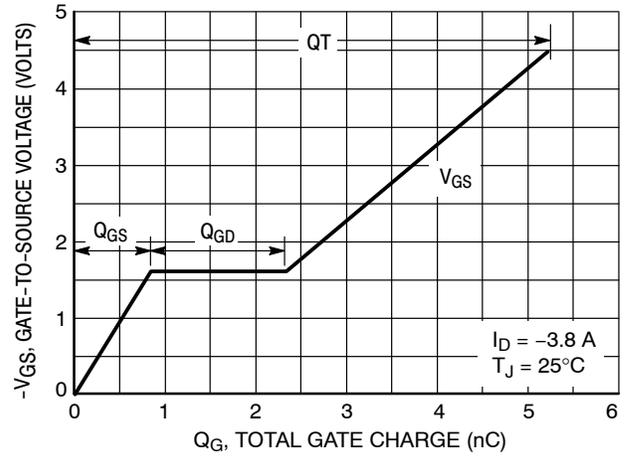


Figure 8. Gate-To-Source and Drain-To-Source Voltage versus Total Charge

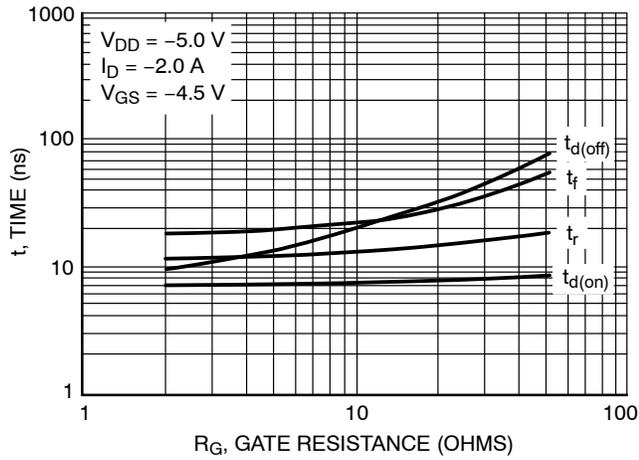


Figure 9. Resistive Switching Time Variation versus Gate Resistance

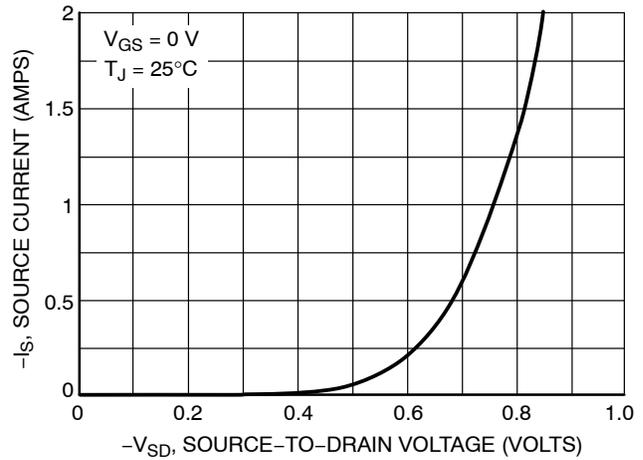


Figure 10. Diode Forward Voltage versus Current

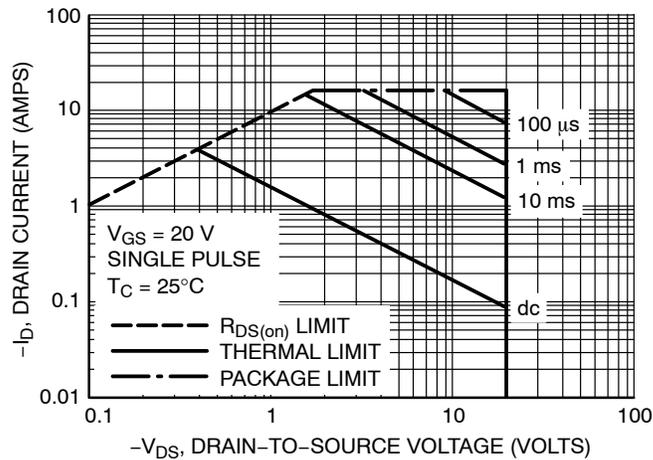


Figure 11. Maximum Rated Forward Biased Safe Operating Area

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TYPICAL PERFORMANCE CURVES ($T_J = 25^\circ\text{C}$ unless otherwise noted)

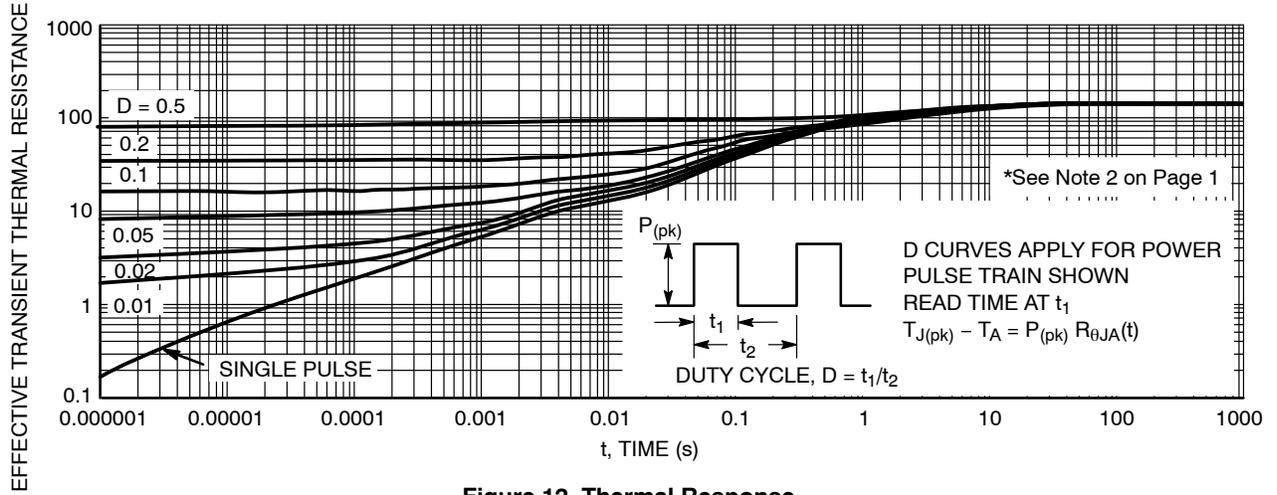


Figure 12. Thermal Response

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TYPICAL SCHOTTKY PERFORMANCE CURVES ($T_J = 25^\circ\text{C}$ unless otherwise noted)

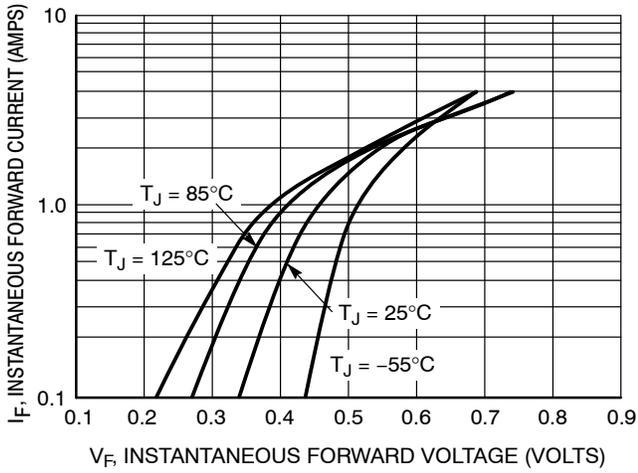


Figure 13. Typical Forward Voltage

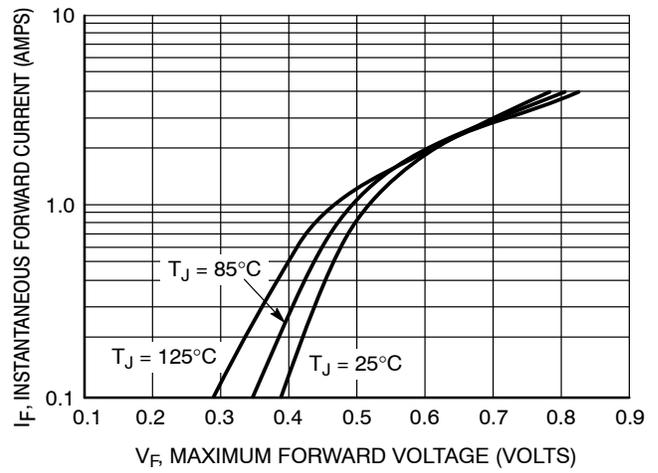


Figure 14. Maximum Forward Voltage

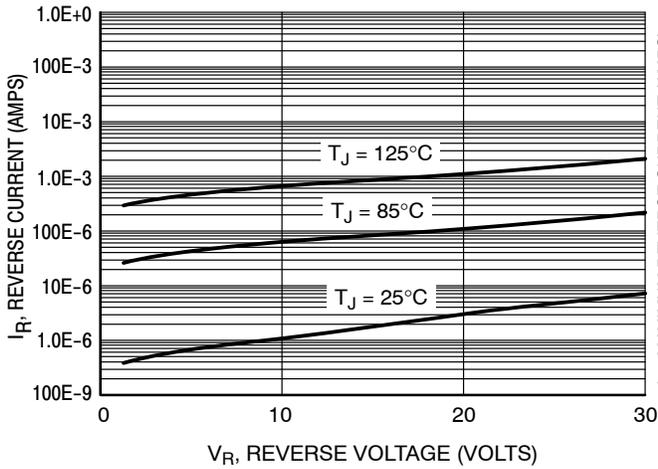


Figure 15. Typical Reverse Current

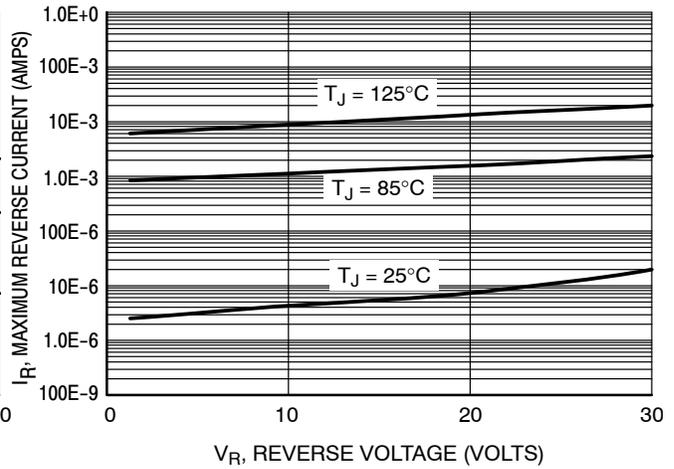
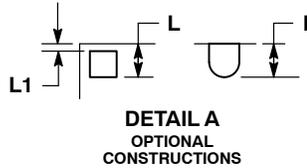
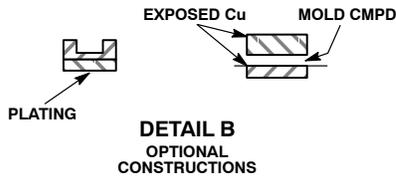
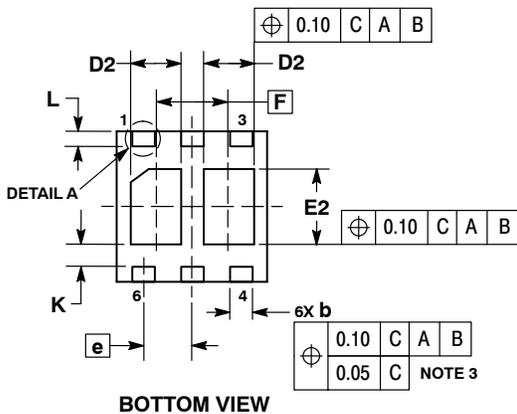
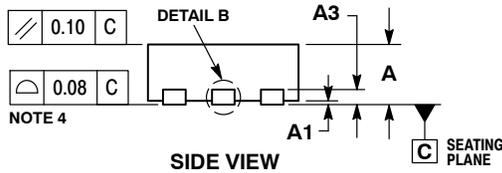
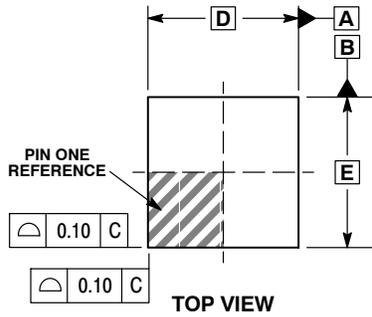


Figure 16. Maximum Reverse Current

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PACKAGE DIMENSIONS

WDFN6 2x2, 0.65P
CASE 506AN
ISSUE G

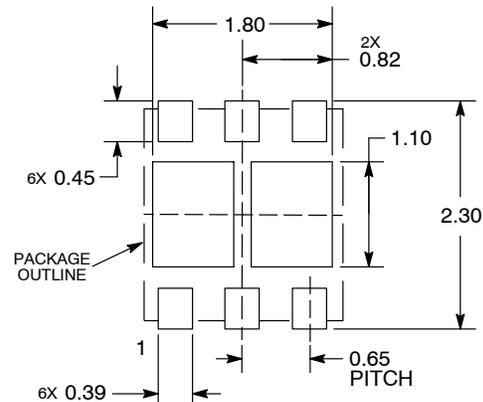


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.30 mm FROM THE TERMINAL TIP.
4. COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.

DIM	MILLIMETERS	
	MIN	MAX
A	0.70	0.80
A1	0.00	0.05
A3	0.20 REF	
b	0.25	0.35
D	2.00 BSC	
D2	0.57	0.77
E	2.00 BSC	
E2	0.90	1.10
e	0.65 BSC	
F	0.95 BSC	
K	0.25 REF	
L	0.20	0.30
L1	---	0.10

SOLDERMASK DEFINED MOUNTING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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